



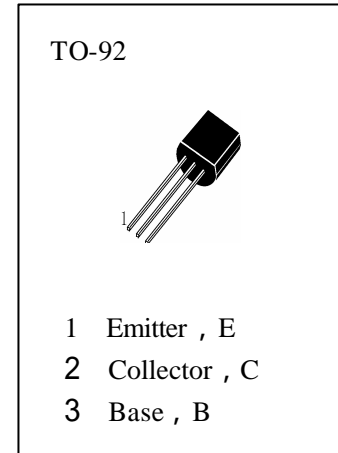
# HE13002

## APPLICATIONS

High Voltage switching And Speed Switching

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25$ )

- $T_{stg}$ —Storage Temperature..... -55~150
- $T_j$ —Junction Temperature.....150
- $P_C$ —Collector Dissipation.....1W
- $V_{CBO}$ —Collector-Base Voltage.....600V
- $V_{CEO}$ —Collector-Emitter Voltage.....400V
- $V_{EBO}$ —Emitter-Base Voltage.....9V
- $I_C$ —Collector Current.....1A



### ELECTRICAL CHARACTERISTICS ( $T_a=25$ )

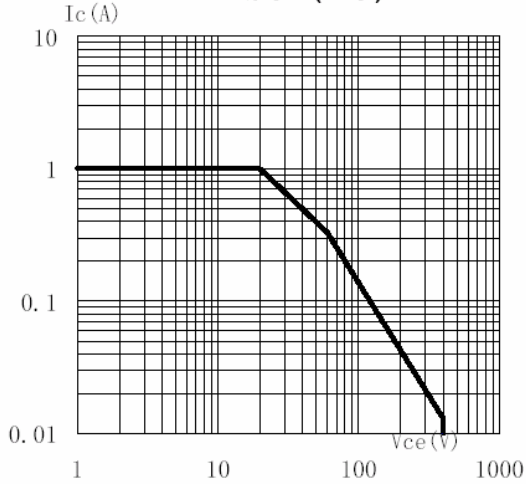
Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CBO}$	Collector-Base Breakdown Voltage	600			V	$I_C=1mA, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	400			V	$I_C=10mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	9			V	$I_E=1mA, I_C=0$
$I_{CBO}$	Collector Cut-off Current			10	$\mu A$	$V_{CB}=500V, I_E=0$
$I_{EBO}$	Emitter-Base Cut-off Current			10	$\mu A$	$V_{EB}=9V, I_C=0$
$H_{FE}$	DC Current Gain	10		40		$V_{CE}=10V, I_C=0.1A$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.5	V	$I_C=0.2A, I_B=40mA$
$V_{CE(sat2)}$	Collector- Emitter Saturation Voltage			1.0	V	$I_C=0.5A, I_B=100mA$
$V_{CE(sat3)}$	Collector- Emitter Saturation Voltage			3	V	$I_C=0.8A, I_B=200mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.2	V	$I_C=0.5A, I_B=100mA$
$f_T$	Current Gain-Bandwidth Product	8			MHZ	$V_{CE}=10V, I_C=0.1A, f=1MHz$
$t_{ON}$	Turn-On Time			1.1	$\mu S$	$V_{CC}=125V, I_C=1A$ $I_{B1}=-I_{B2}=0.2A$ $R_L=125$
$t_{STG}$	Storage Time			4.0	$\mu S$	
$t_F$	Fall Time			0.7	$\mu S$	

### $h_{FE}$ Classification

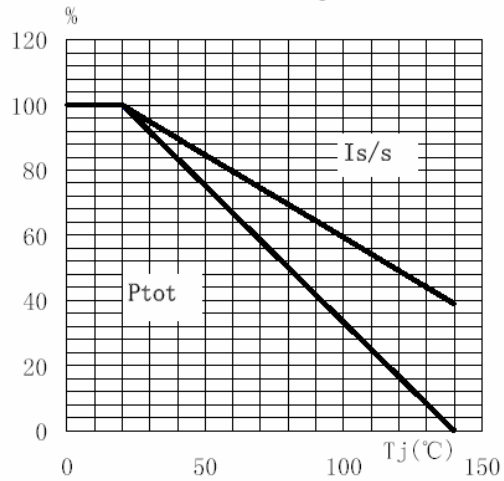
H1	H2	H3	H4	H5
10-16	14-21	19-26	24-31	29-40



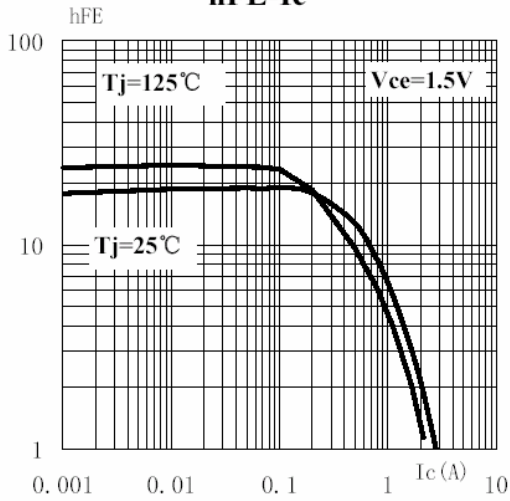
### SOA(DC)



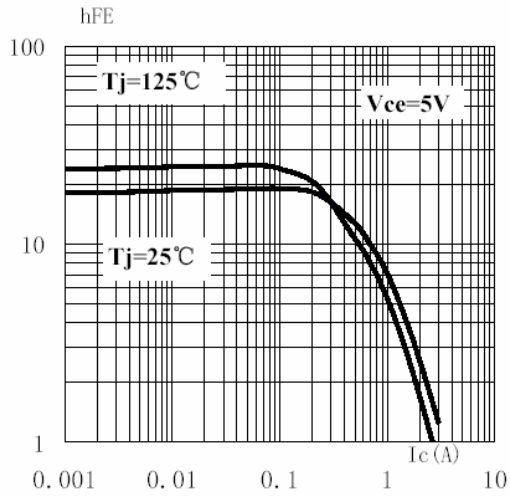
### $P_c \propto T_j$



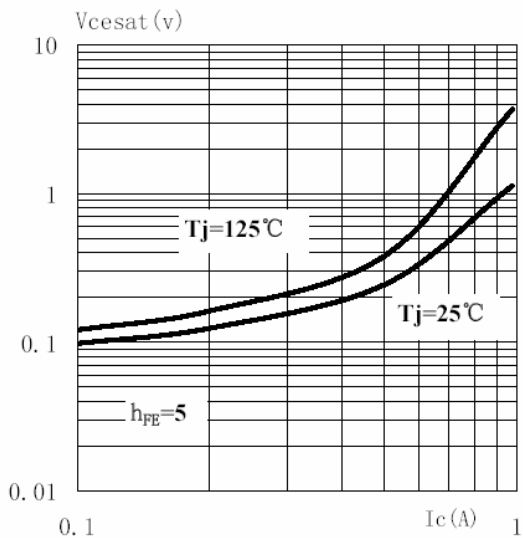
### hFE-Ic



### hFE-Ic



### $V_{cesat}$ -Ic



### $V_{besat}$ -Ic

